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# **DMG204A0**

## Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Halogen-free / RoHS compliant
   (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

## ■ Marking Symbol: C2

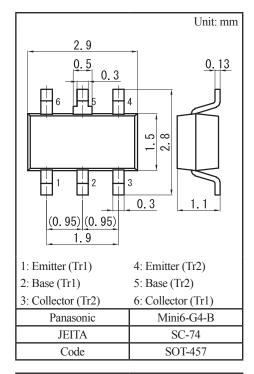
### ■ Basic Part Number

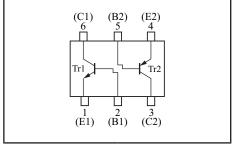
DSC2501 + DSA2401 (Individual)

### ■ Packaging

## ■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter		Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	25	V
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V
	Emitter-base voltage (Collector open)	$V_{\rm EBO}$	12	V
	Collector current	$I_{C}$	0.5	A
	Peak collector current	$I_{CP}$	1	A
Tr2	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-15	V
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-10	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V
	Collector current	$I_{C}$	-0.5	A
	Peak collector current	$I_{CP}$	-1	A
Overall	Total power dissipation	$P_{T}$	300	mW
	Junction temperature	$T_{j}$	150	°C
	Operating ambient temperature	T <sub>opr</sub>	-40 to +85	°C
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C





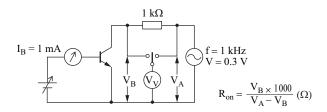
## ■ Electrical Characteristics $T_a = 25$ °C±3°C

## • Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu A, I_E = 0$	25			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu A, I_C = 0$	12			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}, I_{E} = 0$			100	nA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$	200		800	_
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_{\rm C} = 0.5  \text{A}, I_{\rm B} = 20  \text{mA}$		0.18	0.40	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}$			1.2	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		6		pF
ON resistance *2	R <sub>on</sub>			1.0		Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. \*1: Pulse measurement
  - \*2: Ron measurement circuit



## • Tr2

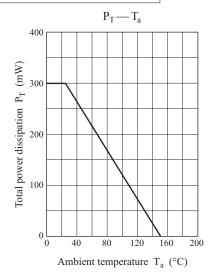
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10  \mu \text{A}, I_{\rm E} = 0$	-15			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -1 \text{ mA}, I_B = 0$	-10			V
Emitter-base voltage (Collector open)	$V_{\mathrm{EBO}}$	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{\rm CB} = -10 \text{ V}, I_{\rm E} = 0$			-100	nA
Forward current transfer ratio *1	h <sub>FE1</sub>	$V_{CE} = -2 \text{ V}, I_{C} = -0.5 \text{ A}$	130		350	
Forward current transfer ratio	h <sub>FE2</sub>	$V_{CE} = -2 \text{ V}, I_{C} = -1 \text{ A}$	60			_
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		-0.8	-1.2	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		18		pF

 $Note) \ 1. \ Measuring \ methods \ are \ based \ on \ JAPANESE \ INDUSTRIAL \ STANDARD \ JIS \ C \ 7030 \ measuring \ methods \ for \ transistors.$ 

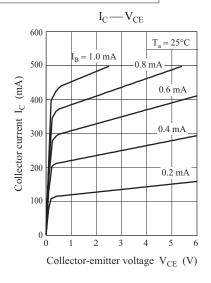
2. \*1: Pulse measurement

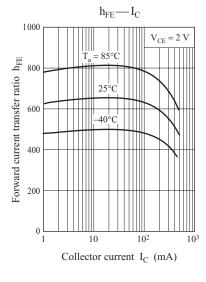
Ver. CED 2

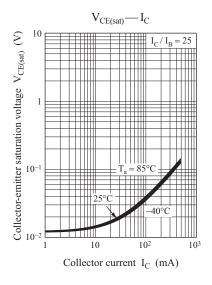
## Common characteristics chart

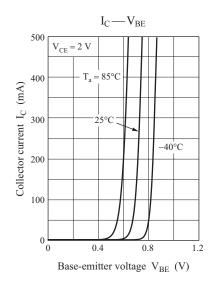


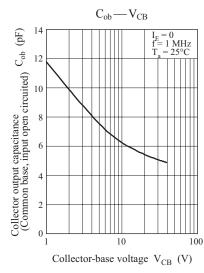
## Characteristics charts of Tr1

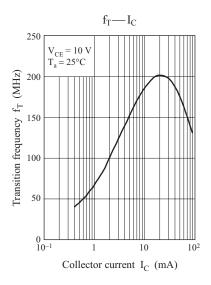


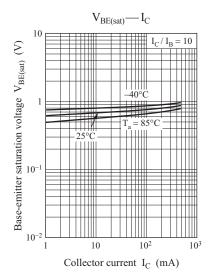




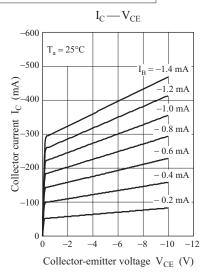


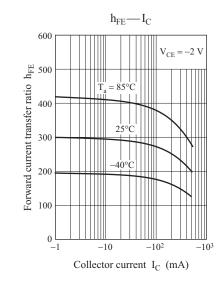


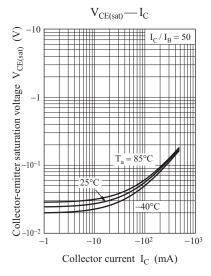


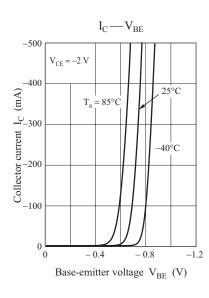


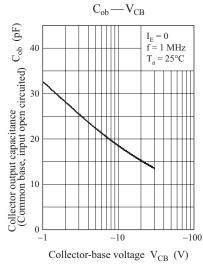
## Characteristics charts of Tr2

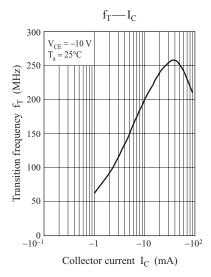


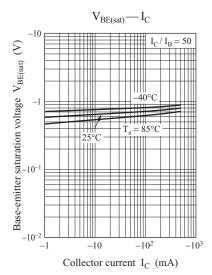








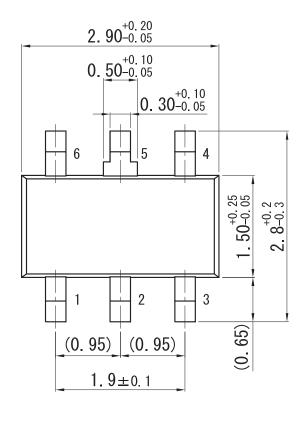


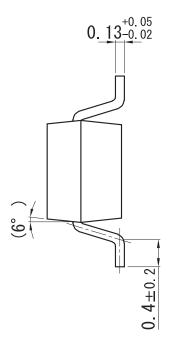


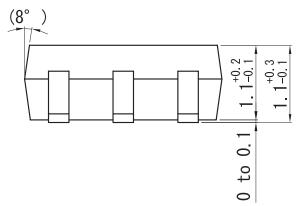
Ver. CED 5

Mini6-G4-B

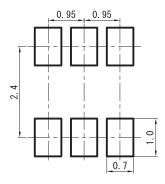
Unit: mm







## ■ Land Pattern (Reference) (Unit: mm)



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